

GENERAL PURPOSE AMPLIFIER

Typical Applications

- Basestation Applications
- Broadband, Low-Noise Gain Blocks
- IF or RF Buffer Amplifiers

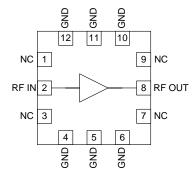
- Driver Stage for Power Amplifiers
- Final PA for Low-Power Applications
- High Reliability Applications

Product Description

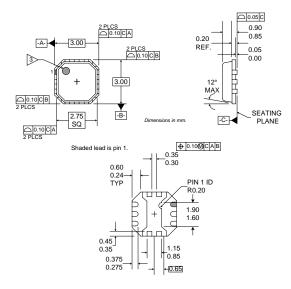
The RF3394 is a general purpose, low-cost RF amplifier IC. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as an easily-cascadable 50Ω gain block. Applications include IF and RF amplification in wireless voice and data communication products operating in frequency bands up to $6000\,\text{MHz}$. The device is self-contained with 50Ω input and output impedances and requires only two external DC-biasing elements to operate as specified. The device is designed for cost effective high reliability in a plastic package. The 3mmx3mm footprint is compatible with standard ceramic and plastic Micro-X packages.

Optimum Technology Matching® Applied

☐ Si BJT ☐ GaAs HBT ☐ GaAs MESFET☐ Si Bi-CMOS☐ ☐ SiGe HBT ☐ Si CMOS☐ ☐ InGaP/HBT ☐ GaN HEMT☐ SiGe Bi-CMOS☐ ☐ GaN HEMT☐ ☐ ☐ GA



Functional Block Diagram



Package Style: QFN, 12-Pin, 3x3

Features

- DC to >6000MHz Operation
- Internally Matched Input and Output
- 20dB Small Signal Gain
- +32dBm Output IP3
- +18dBm Output Power
- Footprint Compatible with Micro-X

Ordering Information

RF3394 General Purpose Amplifier
RF3394 PCBA Fully Assembled Evaluation Board

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RF3394

Absolute Maximum Ratings

Parameter	Rating	Unit
Input RF Power	+13	dBm
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-60 to +150	°C



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Parameter	Specification		Unit	Condition		
Farameter	Min.	Тур.	Max.	Offic	Condition	
Overall					T=25 °C, I _{CC} =65 mA (See Note 1.)	
Frequency Range		DC to >6000		MHz		
3dB Bandwidth		3		GHz		
Gain	18.7	20.2		dB	Freq=500MHz	
	18.5	20.0	21.0	dB	Freq=850MHz	
	17.0	18.7	22.0	dB	Freq=2000MHz	
		16.7		dB	Freq=3000MHz	
		15.7			Freq=4000MHz	
		12.1			Freq=6000MHz	
Noise Figure		3.5		dB	Freq=2000MHz	
Input VSWR		<1.8:1			In a 50Ω system, <500MHz	
		<1.25:1			In a 50Ω system, 500MHz to 5000MHz	
		<2.2:1			In a 50Ω system, 5000MHz to 6000MHz	
Output VSWR		<2.0:1			In a 50Ω system, <500MHz	
		<1.35:1			In a 50Ω system, 500MHz to 4000MHz	
0 () (10	00.0	<1.8:1		ID.	In a 50Ω system, 4000MHz to 6000MHz	
Output IP ₃	+29.0	+32.0		dBm	Freq=2000MHz	
Output P _{1dB}		+17.5		dBm	Freq=2000MHz	
Reverse Isolation		22.0		dB	Freq=2000MHz	
Thermal					I _{CC} =65mA, P _{DISS} =274mW. (See Note 3.)	
Theta _{JC}		147		°C/W	V _{PIN} =4.2V	
Maximum Measured Junction Temperature at DC Bias Con- ditions		139		°C	T _{AMB} =+85°C	
Mean Time To Failure		3065		years	T _{AMB} =+85°C	
Power Supply					With 22Ω bias resistor	
Device Operating Voltage	4.4	4.5	4.6	V	At pin 8 with I _{CC} =65mA	
	5.5	5.9	6.5	V	At evaluation board connectors, I _{CC} =65mA	
Operating Current			80	mA	See Note 2.	

Note 1: All specification and characterization data has been gathered on standard FR-4 evaluation boards. These evaluation boards are not optimized for frequencies above 2.5GHz. Performance above 2.5GHz may improve if a high performance PCB is used.

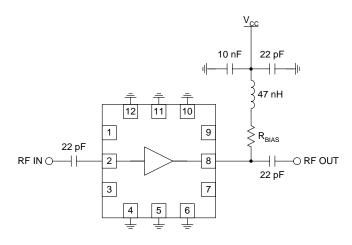
Note 2: The RF3398 must be operated at or below 80mA in order to achieve the thermal performance listed above. While the RF3398 may be operated at higher bias currents, 65mA is the recommended bias to ensure the highest possible reliability and electrical performance.

Note 3: Because of process variations from part to part, the current resulting from a fixed bias voltage will vary. As a result, caution should be used in designing fixed voltage bias circuits to ensure the worst case bias current does not exceed 80 mA over all intended operating conditions.

4-584 Rev A12 040224

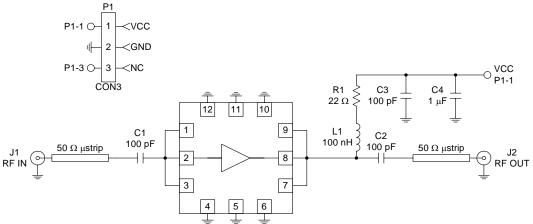
Pin	Function	Description	Interface Schematic
1	NC	No internal connections. It is not necessary to ground this pin.	
2	RF IN	RF input pin. This pin is NOT internally DC blocked. A DC blocking capacitor, suitable for the frequency of operation, should be used in most applications. DC coupling of the input is not allowed, because this will override the internal feedback loop and cause temperature instability.	
3	NC	No internal connections. It is not necessary to ground this pin.	
4	GND	Ground connection.	
5	GND	Ground connection.	
6	GND	Ground connection.	
7	NC	No internal connections. It is not necessary to ground this pin.	
8	RF OUT	RF output and bias pin. Biasing is accomplished with an external series resistor and choke inductor to $V_{\rm CC}$. The resistor is selected to set the DC current into this pin to a desired level. The resistor value is determined by the following equation: $R = \frac{(V_{SUPPLY} - V_{DEVICE})}{I_{CC}}$ Because DC is present on this pin, a DC blocking capacitor, suitable for the frequency of operation, should be used in most applications. The supply side of the bias network should also be well bypassed.	RF IN O
9	NC	No internal connections. It is not necessary to ground this pin.	
10	GND	Ground connection.	
11	GND	Ground connection.	
12	GND	Ground connection.	
Die Flag	GND	Ground connection. To ensure best performance, avoid placing ground vias directly beneath the part.	

Application Schematic



Evaluation Board Schematic

(Download Bill of Materials from www.rfmd.com.)



NOTE:

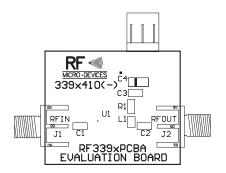
Evaluation board optimized for frequencies above 300 MHz and below 2.5 GHz. For operation below 300 MHz the value of inductor L1 and capcitors C1 and C2 should be increased.

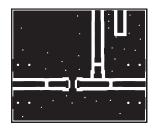
4-586 Rev A12 040224

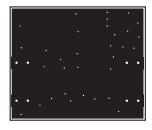
Evaluation Board Layout Board Size 1.195" x 1.000"

Board Thickness 0.033", Board Material FR-4

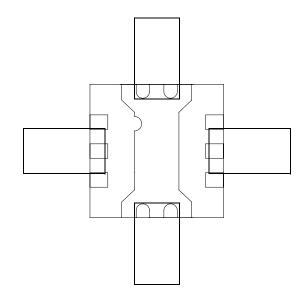
Note: A small amount of ground inductance is required to achieve datasheet performance. The necessary inductance may be generated by ensuring that no ground vias are placed directly below the footprint of the part.

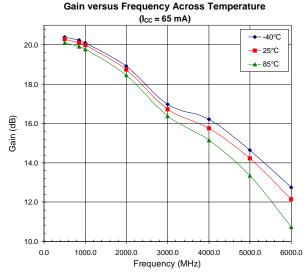


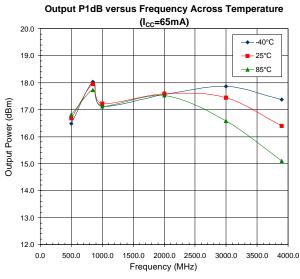


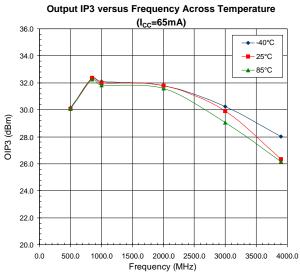


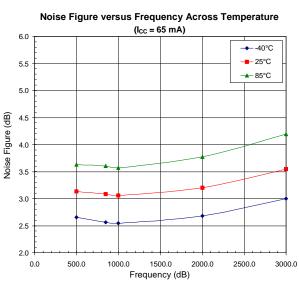
Overlay of Suggested Micro-X and 3mmx3mm Layouts Showing Compatibility

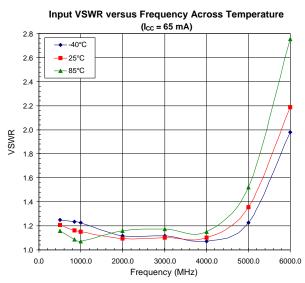


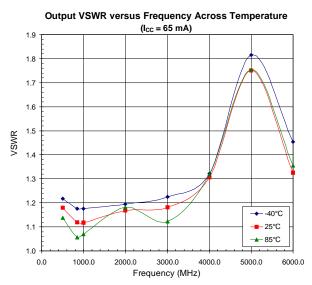




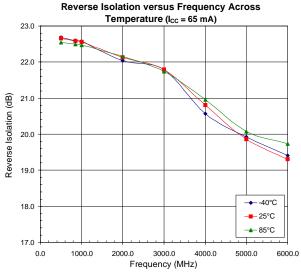


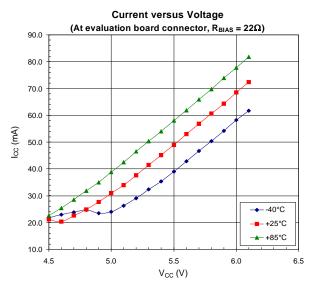


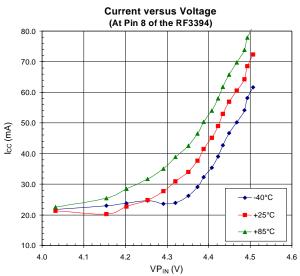


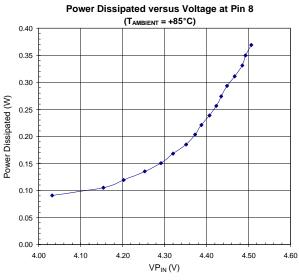


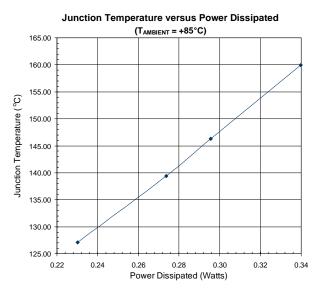
4-588 Rev A12 040224











PCB Design Requirements

PCB Surface Finish

The PCB surface finish used for RFMD's qualification process is Electroless Nickel, immersion Gold. Typical thickness is 3µinch to 8µinch Gold over 180µinch Nickel.

PCB Land Pattern Recommendation

PCB land patterns are based on IPC-SM-782 standards when possible. The pad pattern shown has been developed and tested for optimized assembly at RFMD; however, it may require some modifications to address company specific assembly processes. The PCB land pattern has been developed to accommodate lead and package tolerances.

PCB Metal Land Mask Pattern

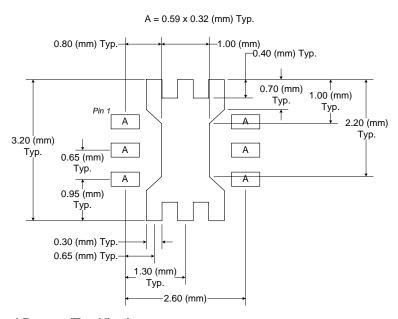


Figure 1. PCB Metal Land Pattern (Top View)

4-590 Rev A12 040224

PCB Solder Mask Pattern

Liquid Photo-Imageable (LPI) solder mask is recommended. The solder mask footprint will match what is shown for the PCB metal land pattern with a 2mil to 3mil expansion to accommodate solder mask registration clearance around all pads. The center-grounding pad shall also have a solder mask clearance. Expansion of the pads to create solder mask clearance can be provided in the master data or requested from the PCB fabrication supplier.

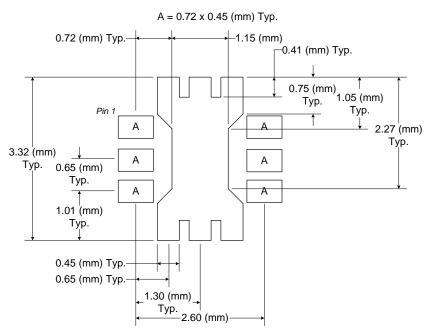


Figure 2. PCB Solder Mask (Top View)

Thermal Pad and Via Design

The PCB metal land pattern has been designed with a thermal pad that matches the exposed die paddle size on the bottom of the device.

Thermal vias are required in the PCB layout to effectively conduct heat away from the package. The via pattern has been designed to address thermal, power dissipation and electrical requirements of the device as well as accommodating routing strategies.

The via pattern used for the RFMD qualification is based on thru-hole vias with 0.203mm to 0.330mm finished hole size on a 0.5mm to 1.2mm grid pattern with 0.025mm plating on via walls. If micro vias are used in a design, it is suggested that the quantity of vias be increased by a 4:1 ratio to achieve similar results.

NOTE: A small amount of ground inductance is required to achieve data sheet performance. The necessary inductance may be generated by ensuring that no ground vias are placed directly below the footprint of the part.

RF3394

4-592 Rev A12 040224